

BISTAR



12BB Half-cut Cell Technology

New circuit design, lower internal current, lower R_s loss
Ga doped wafer, attenuation $<2\%$ (1st year) / $\leq 0.55\%$ (Linear)



Significantly Lower the Risk of Hot Spot

Special circuit design with much lower hot spot temperature



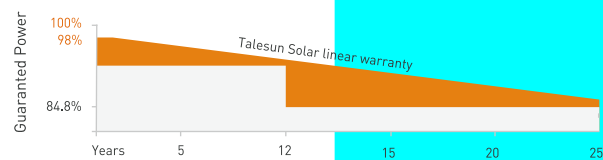
Lower LCOE

2% more power genera



IP68 Junction Box

High waterproof level



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